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## **ON Semiconductor**®

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June 2014



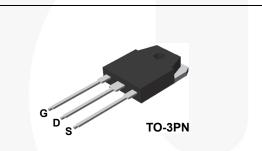
## FQA24N60 N-Channel QFET<sup>®</sup> MOSFET 600 V, 23.5 A, 240 mΩ

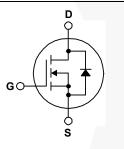
## Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### Features

- + 23.5 A, 600 V,  $R_{DS(on)}$  = 240 m $\Omega$  (Max.) @ V\_{GS} = 10 V,  $I_{D}$  = 11.8 A
- Low Gate Charge (Typ. 110 nC)
- Low Crss (Typ. 56 pF)
- 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

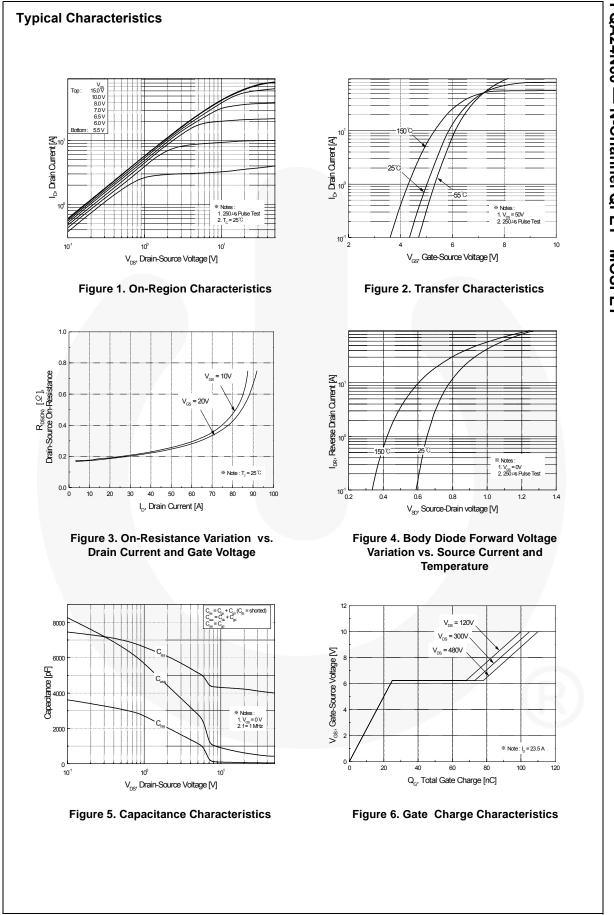
Symbol	Parameter	FQA24N60	Unit	
V <sub>DSS</sub>	Drain-Source Voltage	600	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )	23.5	A	
	- Continuous (T <sub>C</sub> = 100°C	14.9	A	
DM	Drain Current - Pulsed	(Note 1)	94	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V	
AS	Single Pulsed Avalanche Energy	(Note 2)	1300	mJ
AR	Avalanche Current	(Note 1)	23.5	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	31	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
<b>D</b>	Power Dissipation (T <sub>C</sub> = 25°C)		310	W
	- Derate above 25°C	2.5	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150		
Γ <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	°C	

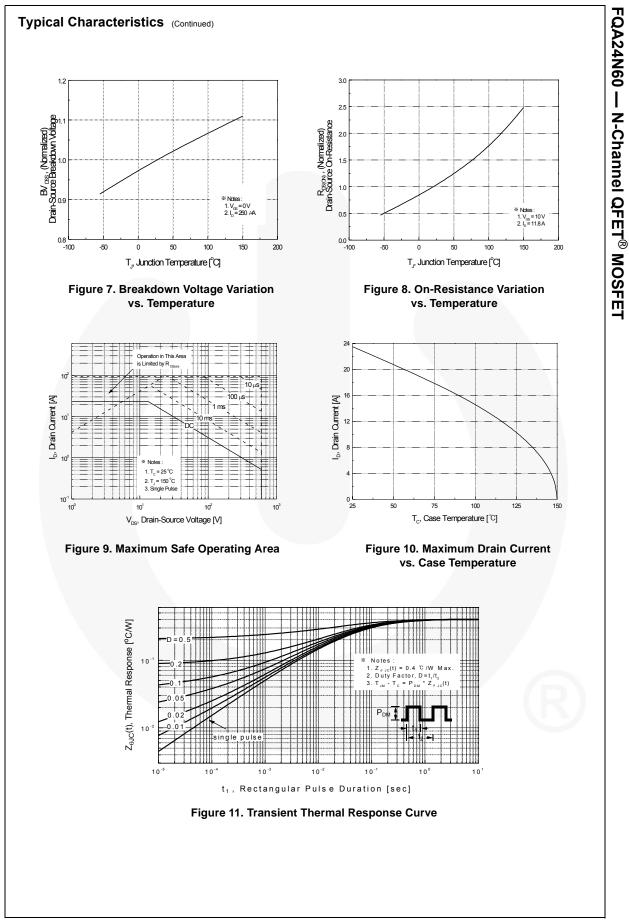
#### **Thermal Characteristics**

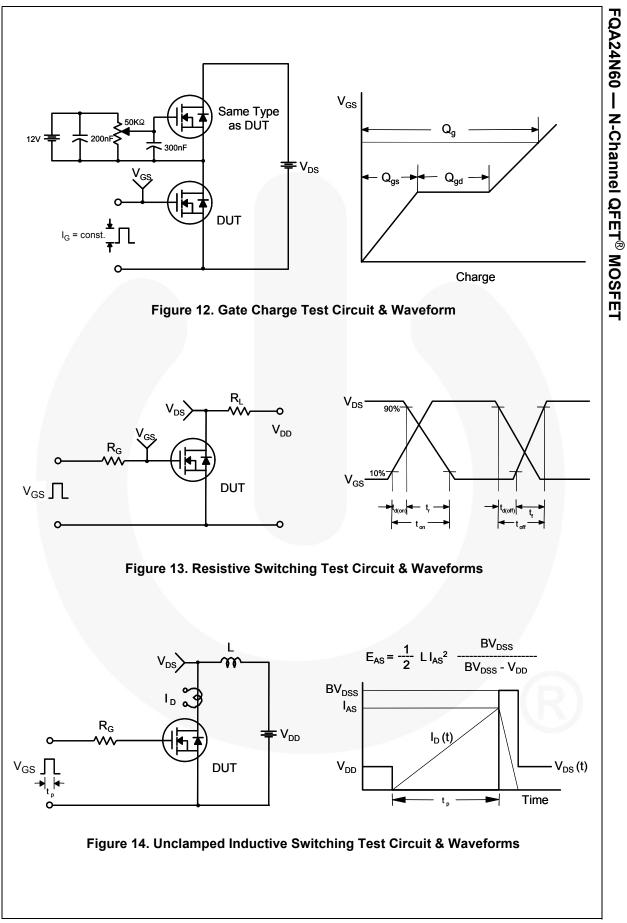
Symbol	Parameter	FQA24N60	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

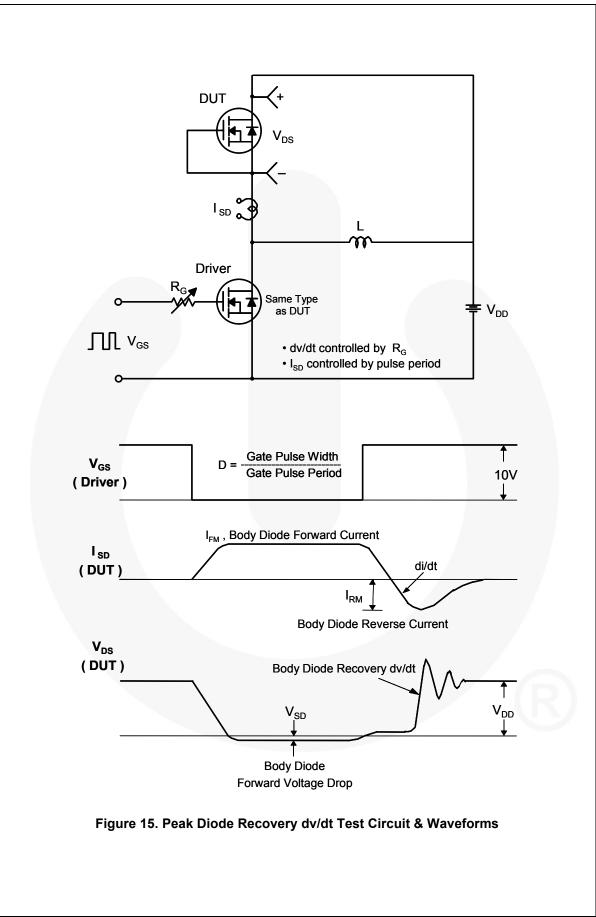
Symbol Off Cha BV <sub>DSS</sub> ΔBV <sub>DSS</sub> ( ΔT <sub>J</sub>	cal Cha racteris	FQA24N60		age	Packing Method	Reel S	Size	Tape W	Mun	Quantity
Symbol Off Cha BV <sub>DSS</sub> ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	<b>racteris</b> Drain-So	aracteristics	TO-3			N//	Ą	N/A		30 units
Symbol Off Cha BV <sub>DSS</sub> ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	<b>racteris</b> Drain-So		T. = 25°C un	less otherwi	se noted					
Off Cha BV <sub>DSS</sub> ΔBV <sub>DSS</sub> / ΔT <sub>J</sub> I <sub>DSS</sub>	Drain-So	Parameter	1 <sub>C</sub> 200 an		Test Conditions		Min.	Тур.	Max.	Unit
BV <sub>DSS</sub> ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Drain-So									-
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>		ource Breakdown Vol	ade	V <sub>GS</sub> = (	Ο V, I <sub>D</sub> = 250 μA		600			V
$/\Delta T_{J}$	Breakdov	down Voltage Temperature								
Ince	Coefficient		$I_D = 250 \ \mu$ A, Referenced to 25°C			0.6		V/°C		
.035	Zero Gate Voltage Drain Current		_	$500 \text{ V}, \text{ V}_{\text{GS}} = 0 \text{ V}$				10	μA	
				$V_{DS} = 480 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$					100	μΑ
I <sub>GSSF</sub>		dy Leakage Current,			$30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$				100	nA
I <sub>GSSR</sub>	Gate-Boo	dy Leakage Current,	Reverse	V <sub>GS</sub> = -	$-30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$				-100	nA
On Cha	racteris	tics								
V <sub>GS(th)</sub>	Gate Thr	reshold Voltage		V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = 250 μA		3.0		5.0	V
R <sub>DS(on)</sub>		ain-Source		V <sub>GS</sub> =	10 V, I <sub>D</sub> = 11.8 A			0.18	0.24	Ω
9 <sub>FS</sub>		Dn-Resistance Forward Transconductance		V <sub>DS</sub> = 50 V, I <sub>D</sub> = 11.8 A				22.5		S
Dvnami	c Chara	acteristics								
C <sub>iss</sub>		pacitance		$V_{\rm DC} = 2$	25 V, V <sub>GS</sub> = 0 V,			4200	5500	pF
C <sub>oss</sub>		apacitance		f = 1.0				550	720	pF
C <sub>rss</sub>	Reverse	Transfer Capacitanc	e					56	75	pF
	na Chai	ractoristics								
	-	racteristics Delay Time						00	100	
t <sub>d(on)</sub> t <sub>r</sub>		Rise Time			$300 \text{ V}, \text{ I}_{\text{D}} = 23.5 \text{ A},$			90 270	190 550	ns
		Delay Time		R <sub>G</sub> = 2	5 7 2			200	410	ns
t <sub>d(off)</sub> t <sub>f</sub>		Fall Time				(Note 4)		170	350	-
Qg		te Charge		V -	190 \/   = 22 E A			110	145	ns
Q <sub>gs</sub>		urce Charge		$V_{DS} = 2$ $V_{GS} = 2$	480 V, I <sub>D</sub> = 23.5 A,			25		nC
	Gale-50			VGS -		(Note 4)		53		nC
-	Gate_Dra	an charge				( ,	-	- 55		ne
Q <sub>gd</sub>	Gate-Dra									
Q <sub>gd</sub> Drain-Se	ource D	oiode Character			0		1	1		
Q <sub>gd</sub> Drain-So	ource D Maximur	n Continuous Drain-S	Source Dic	de Forwa	ard Current				23.5	Α
Q <sub>gd</sub> Drain-So I <sub>S</sub> I <sub>SM</sub>	ource D Maximun Maximun	n Continuous Drain-S n Pulsed Drain-Sourc	Source Dic ce Diode F	de Forward C	ard Current				23.5 94	Α
Q <sub>gd</sub> Drain-So I <sub>S</sub> I <sub>SM</sub> V <sub>SD</sub>	ource D Maximun Maximun Drain-So	n Continuous Drain-S n Pulsed Drain-Sourd purce Diode Forward	Source Dic ce Diode F	ode Forward C Forward C V <sub>GS</sub> = 0	ard Current Current O V, I <sub>S</sub> = 23.5 A					
Q <sub>gd</sub>	ource D Maximur Maximur Drain-So Reverse	n Continuous Drain-S n Pulsed Drain-Sourc	Source Dic ce Diode F	ode Forward C Forward C $V_{GS} = 0$ $V_{GS} = 0$	ard Current		  		94	Α

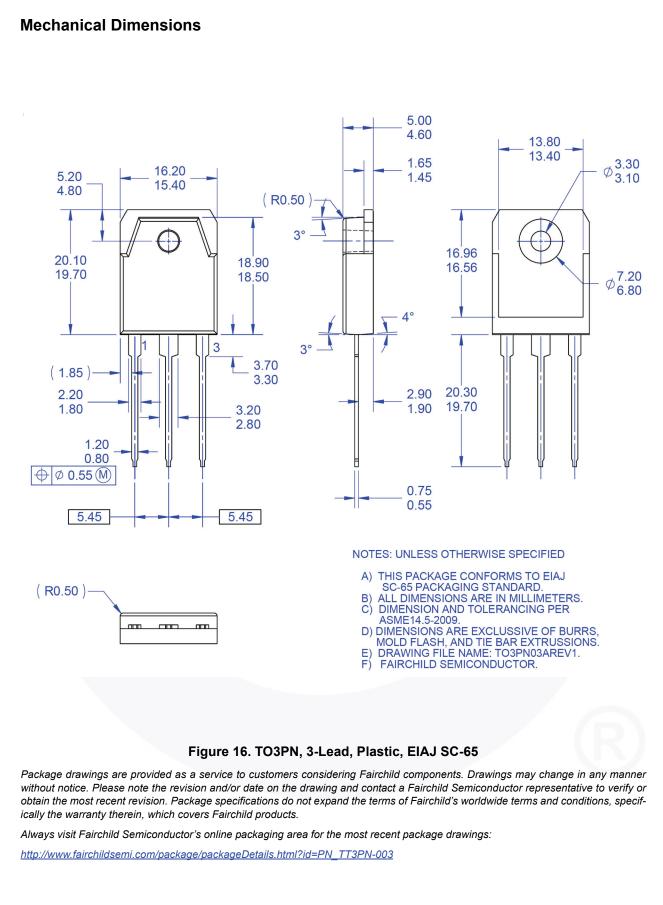
FQA24N60 — N-Channel QFET<sup>®</sup> MOSFET













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